

Clean Claims:

Q1 sub c1 → 5. (Amended) A structure of claim 17, wherein the drain contact region is split into at least one first drain contact portion located near the gate, and at least one second drain contact portion.

Q2 sub c2 → 7. (Amended) A structure of claim 17, wherein the structure includes multiple emitters outside at least part of the drain contact region.

sub c3 → Q3 11. (Amended) A high holding voltage LVTSCR-like structure, comprising an emitter, a drain, and a floating drain, wherein the emitter is located so that at least part of the drain is located between the gate and emitter.

12. (Amended) A structure of claim 11, wherein the drain is split into at least one first drain portion located near the gate, and at least one second drain portion.

14. A structure of claim 11, wherein the emitter comprises a plurality of emitter regions.

15. A structure of claim 12, wherein the emitter comprises a plurality of emitter regions.

Q4 sub c5 → 16. (Amended) A structure of claim 12, wherein the floating drain and drain are separated by a shallow trench isolation region.

sub c6 → Q5 17. A LVTSCR-like ESD protection structure, comprising a drain contact region, a p+ emitter, and a gate, wherein at least part of the drain contact region is located between the p+ emitter and the gate.

18. A structure of claim 17, further comprising a floating drain located between the gate and the p+ emitter.